

RJH1CV7DPQ-E0

1200V - 35A - IGBT

Application: Inverter

R07DS0525EJ0500

Rev.5.00

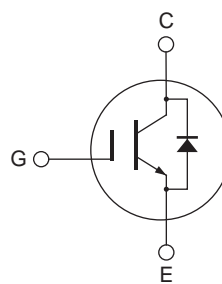
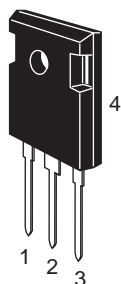
May 24, 2012

Features

- Short circuit withstand time (5 μ s typ.)
- Low collector to emitter saturation voltage
 $V_{CE(sat)} = 1.8$ V typ. (at $I_C = 35$ A, $V_{GE} = 15$ V, $T_a = 25^\circ\text{C}$)
- Built-in fast recovery diode ($t_{rr} = 200$ ns typ.) in one package
- Trench gate and thin wafer technology
- High speed switching
 $t_f = 280$ ns typ. (at $V_{CC} = 600$ V, $V_{GE} = 15$ V, $I_C = 35$ A, $R_g = 5$ Ω , $T_a = 25^\circ\text{C}$, inductive load)

Outline

RENESAS Package code: PRSS0003ZE-A
(Package name: TO-247)



1. Gate
2. Collector
3. Emitter
4. Collector

Absolute Maximum Ratings

($T_a = 25^\circ\text{C}$)

| Item | | Symbol | Ratings | Unit |
|--|---------------------------|----------------------------------|-------------|---------------------------|
| Collector to emitter voltage / diode reverse voltage | | V_{CES} / V_R | 1200 | V |
| Gate to emitter voltage | | V_{GES} | ± 30 | V |
| Collector current | $T_c = 25^\circ\text{C}$ | I_C | 70 | A |
| | $T_c = 100^\circ\text{C}$ | I_C | 35 | A |
| Collector peak current | | $i_{c(peak)}$ ^{Note1} | 105 | A |
| Collector to emitter diode forward current | | I_{DF} | 35 | A |
| Collector to emitter diode forward peak current | | $i_{DF(peak)}$ ^{Note1} | 105 | A |
| Collector dissipation | | P_C ^{Note2} | 320 | W |
| Junction to case thermal resistance (IGBT) | | θ_{j-c} ^{Note2} | 0.39 | $^\circ\text{C}/\text{W}$ |
| Junction to case thermal resistance (Diode) | | θ_{j-cd} ^{Note2} | 0.69 | $^\circ\text{C}/\text{W}$ |
| Junction temperature | | T_j | 150 | $^\circ\text{C}$ |
| Storage temperature | | T_{stg} | -55 to +150 | $^\circ\text{C}$ |

Notes: 1. $PW \leq 10$ μ s, duty cycle $\leq 1\%$

2. Value at $T_c = 25^\circ\text{C}$

Electrical Characteristics

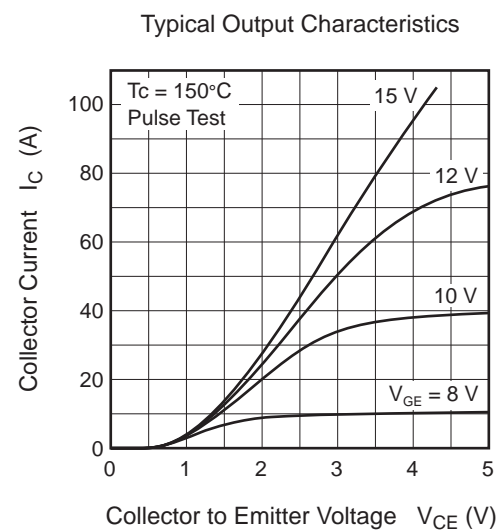
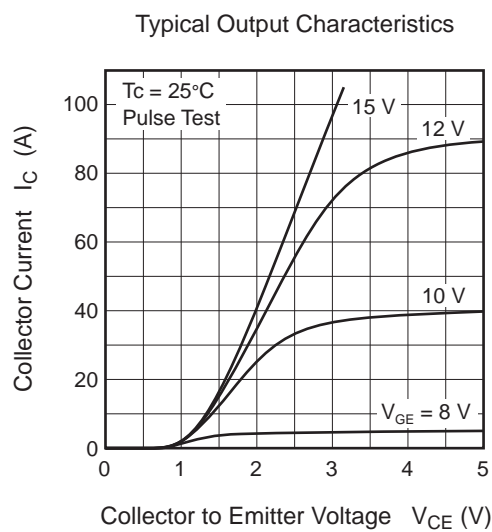
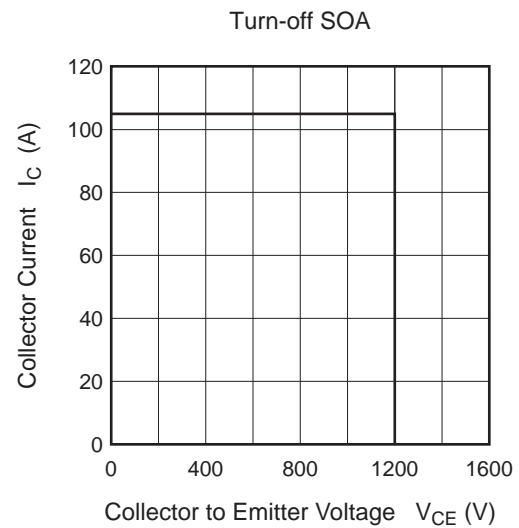
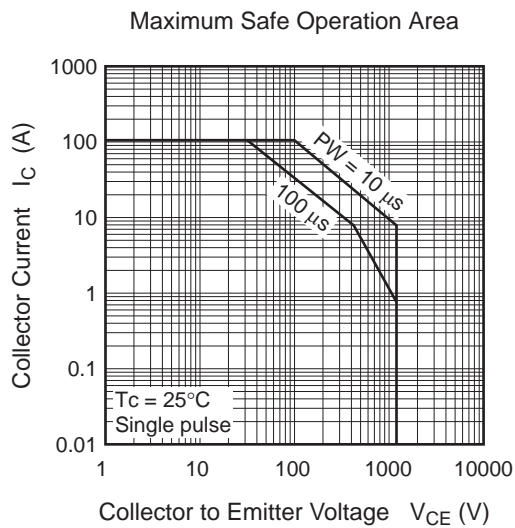
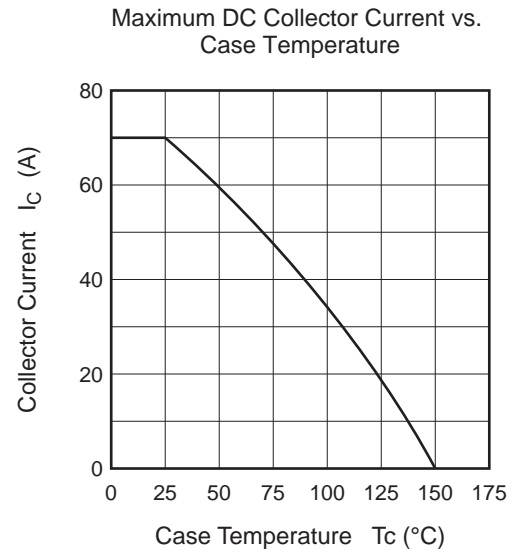
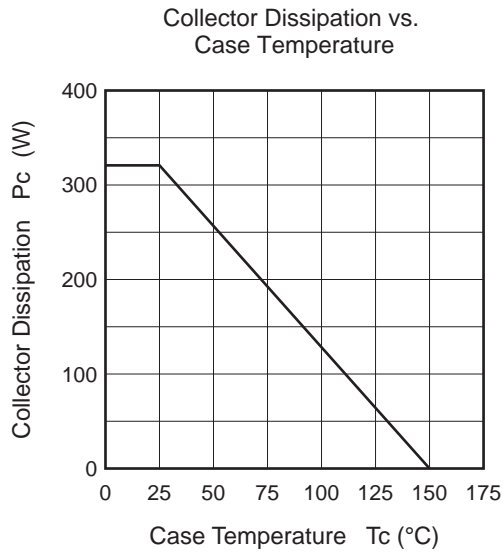
(Ta = 25°C)

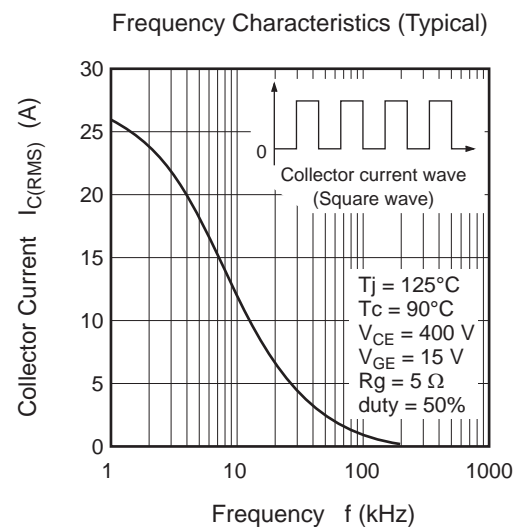
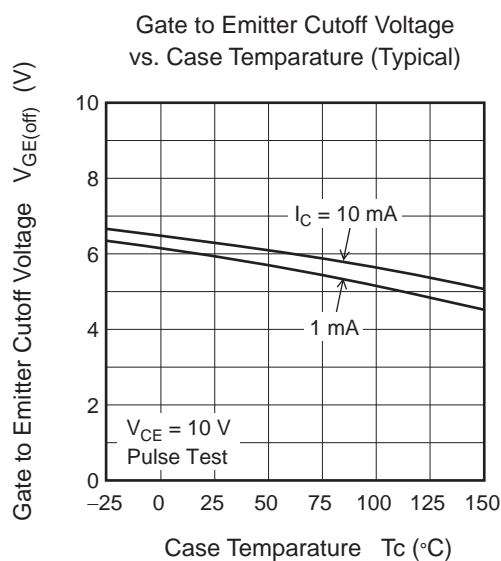
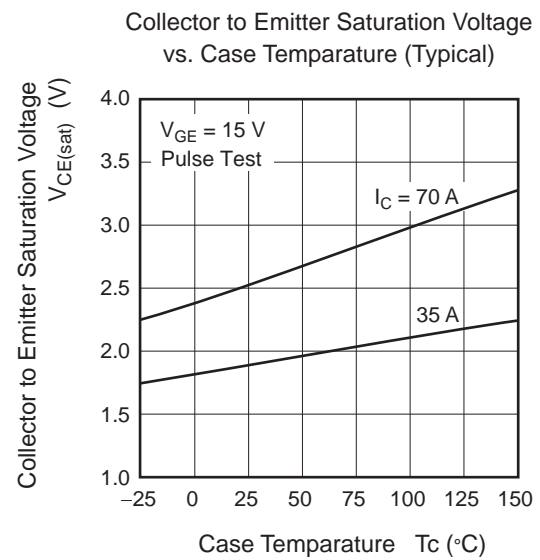
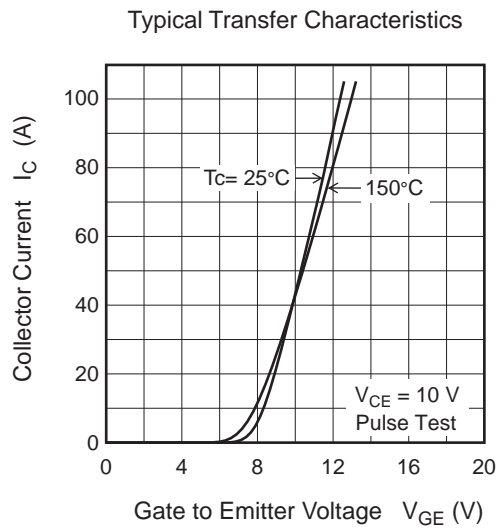
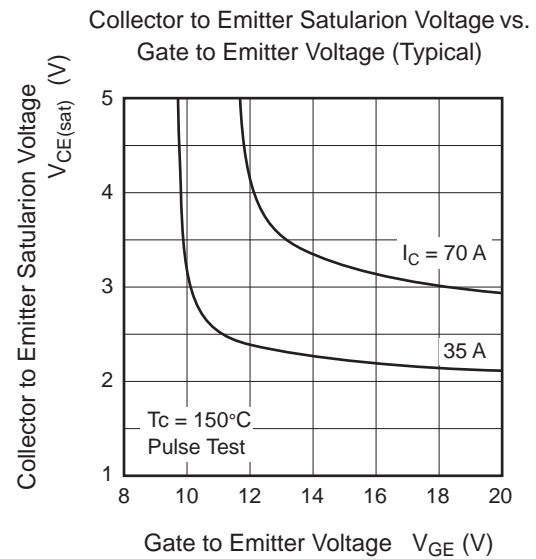
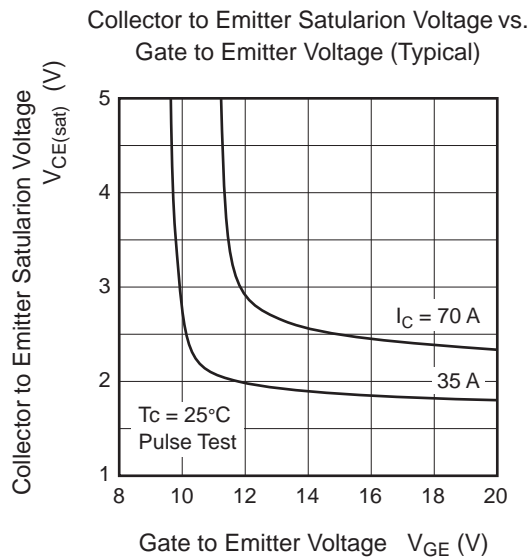
| Item | Symbol | Min | Typ | Max | Unit | Test Conditions |
|---|---------------|------|------|---------|---------|--|
| Collector to emitter breakdown voltage | $V_{(BR)CES}$ | 1200 | — | — | V | $I_C = 10 \mu A, V_{GE} = 0$ |
| Zero gate voltage collector current / Diode reverse current | I_{CES}/I_R | — | — | 5 | μA | $V_{CE} = 1200 V, V_{GE} = 0$ |
| Gate to emitter leak current | I_{GES} | — | — | ± 1 | μA | $V_{GE} = \pm 30 V, V_{CE} = 0$ |
| Gate to emitter cutoff voltage | $V_{GE(off)}$ | 4.5 | — | 6.5 | V | $V_{CE} = 10 V, I_C = 1 mA$ |
| Collector to emitter saturation voltage | $V_{CE(sat)}$ | — | 1.8 | 2.3 | V | $I_C = 35 A, V_{GE} = 15 V$ ^{Note3} |
| | $V_{CE(sat)}$ | — | 2.5 | — | V | $I_C = 70 A, V_{GE} = 15 V$ ^{Note3} |
| Input capacitance | C_{ies} | — | 2075 | — | pF | $V_{CE} = 25 V$ |
| Output capacitance | C_{oes} | — | 100 | — | pF | $V_{GE} = 0$ |
| Reverse transfer capacitance | C_{res} | — | 55 | — | pF | $f = 1 MHz$ |
| Total gate charge | Q_g | — | 166 | — | nC | $V_{GE} = 15 V$ |
| Gate to emitter charge | Q_{ge} | — | 20 | — | nC | $V_{CE} = 300 V$ |
| Gate to collector charge | Q_{gc} | — | 95 | — | nC | $I_C = 35 A$ |
| Turn-on delay time | $t_{d(on)}$ | — | 53 | — | ns | $V_{CC} = 600 V$ |
| Rise time | t_r | — | 45 | — | ns | $V_{GE} = 15 V$ |
| Turn-off delay time | $t_{d(off)}$ | — | 185 | — | ns | $I_C = 35 A$ |
| Fall time | t_f | — | 280 | — | ns | $R_g = 5 \Omega$ |
| Turn-on energy | E_{on} | — | 3.2 | — | mJ | Inductive load |
| Turn-off energy | E_{off} | — | 2.5 | — | mJ | |
| Total switching energy | E_{total} | — | 5.7 | — | mJ | |
| Short circuit withstand time | t_{sc} | — | 5 | — | μs | $V_{CC} \leq 720 V, V_{GE} = 15 V$ $T_C \leq 125^\circ C$ |

| | | | | | | |
|-----------------------------------|----------|---|-----|---|---------|-------------------------------|
| FRD forward voltage | V_F | — | 2.1 | — | V | $I_F = 35 A$ ^{Note3} |
| FRD reverse recovery time | t_{rr} | — | 200 | — | ns | $I_F = 35 A$ |
| FRD reverse recovery charge | Q_{rr} | — | 0.7 | — | μC | $di_F/dt = 100 A/\mu s$ |
| FRD peak reverse recovery current | I_{rr} | — | 9.6 | — | A | |

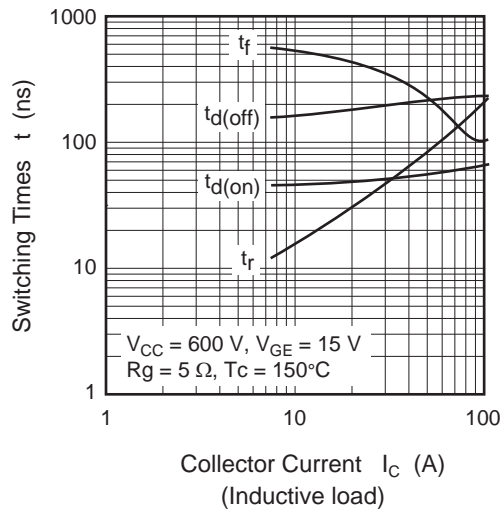
Notes: 3. Pulse test.

Main Characteristics

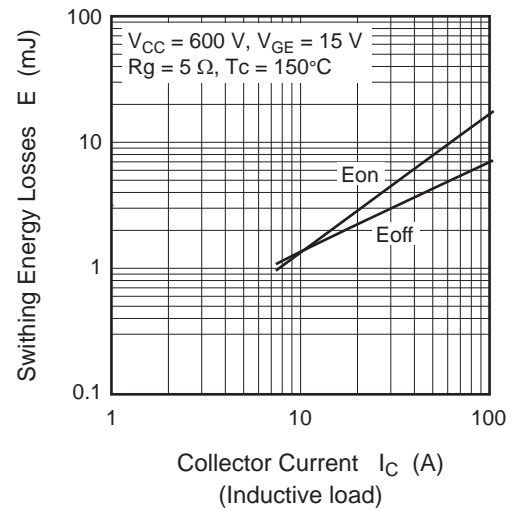




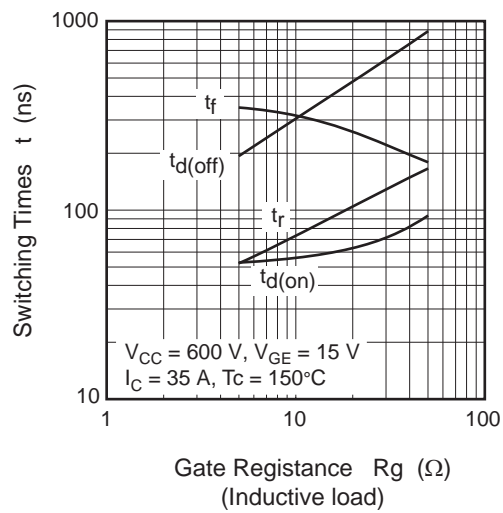
Switching Characteristics (Typical) (1)



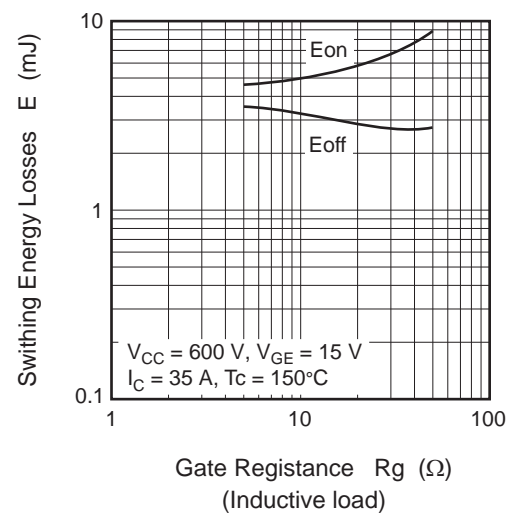
Switching Characteristics (Typical) (2)



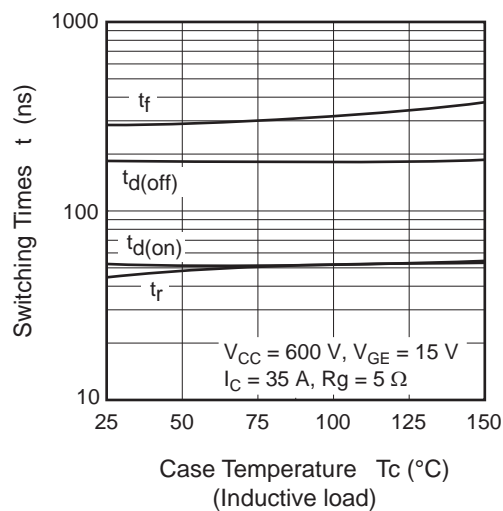
Switching Characteristics (Typical) (3)



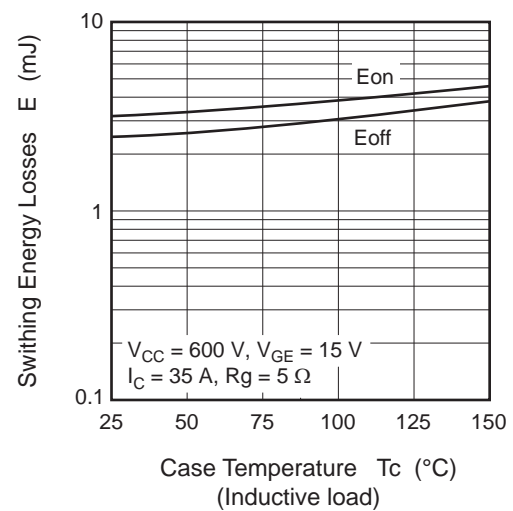
Switching Characteristics (Typical) (4)



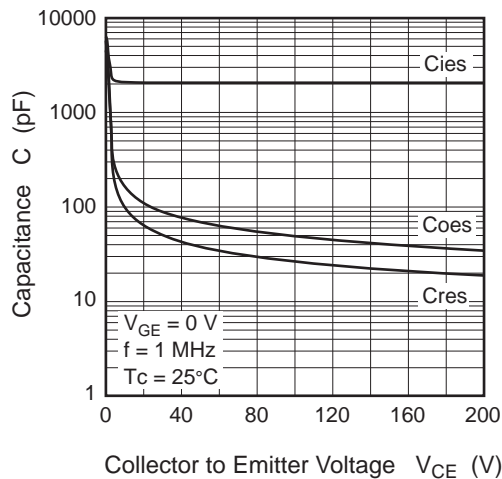
Switching Characteristics (Typical) (5)



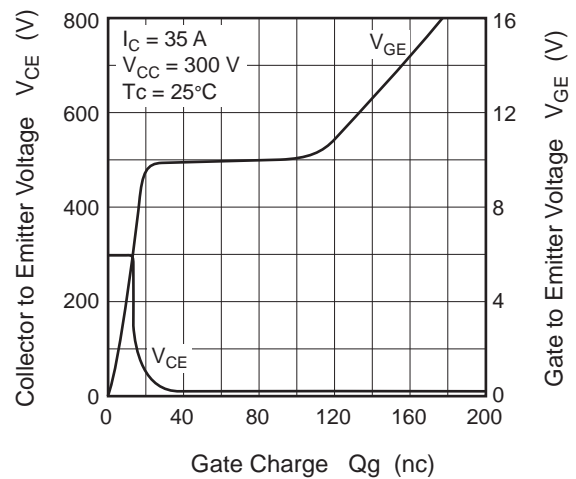
Switching Characteristics (Typical) (6)



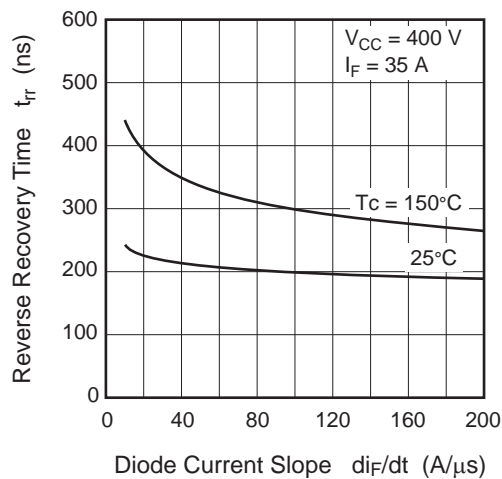
Typical Capacitance vs.
Collector to Emitter Voltage



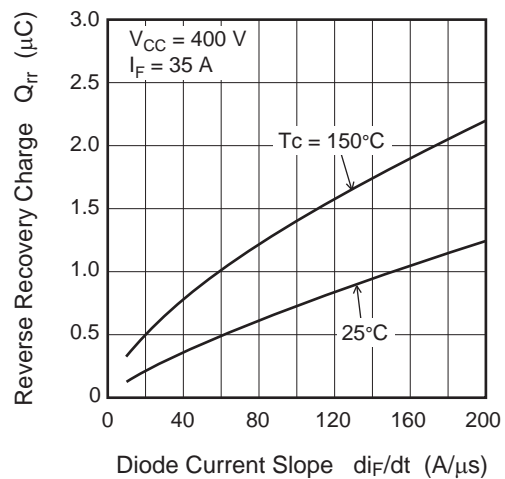
Dynamic Input Characteristics (Typical)



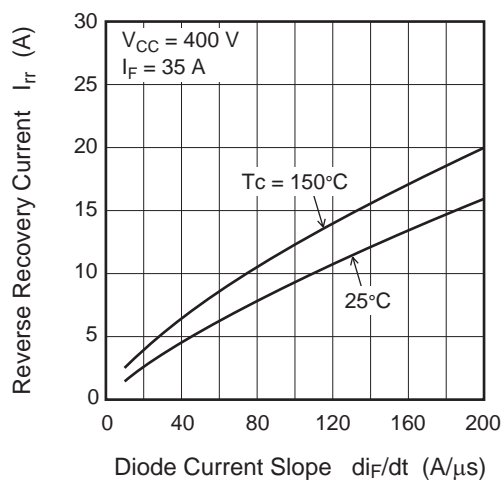
Reverse Recovery Time vs.
Diode Current Slope (Typical)



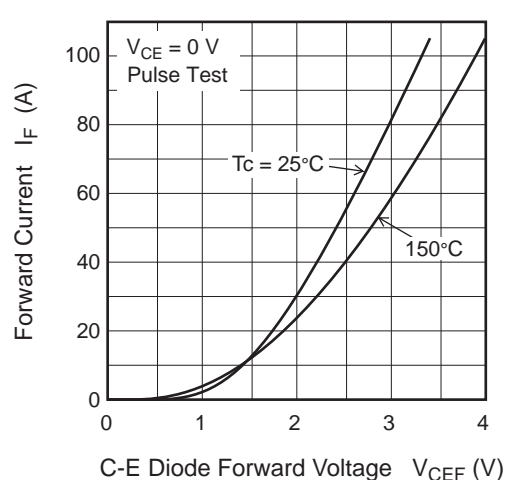
Reverse Recovery Charge vs.
Diode Current Slope (Typical)

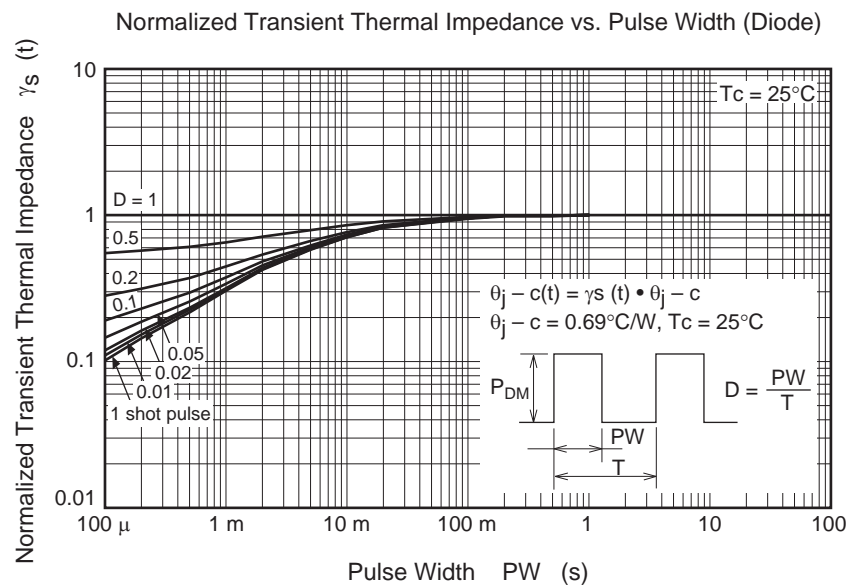
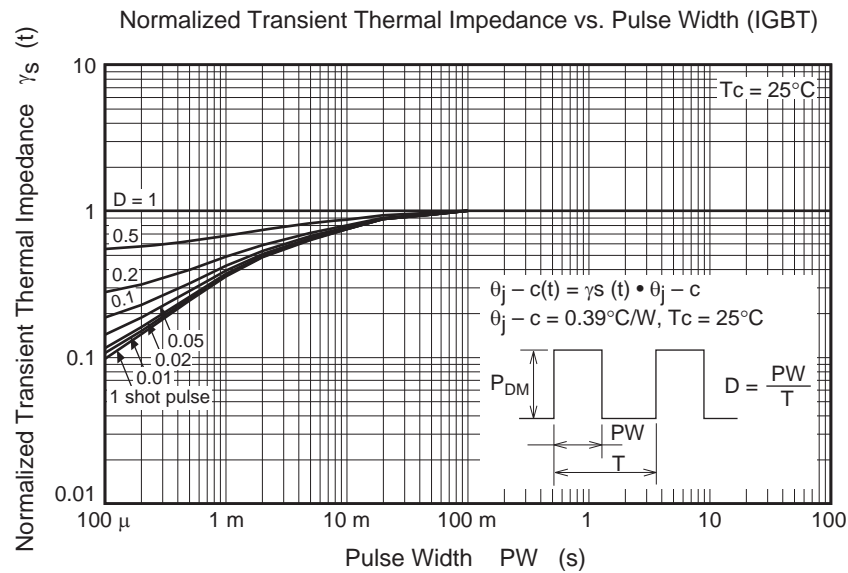


Reverse Recovery Current vs.
Diode Current Slope (Typical)

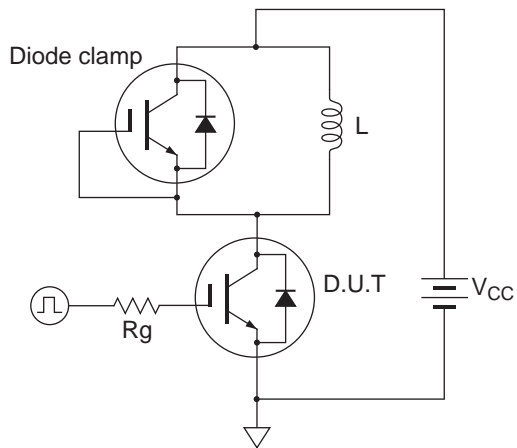


Forward Current vs. Forward Voltage (Typical)

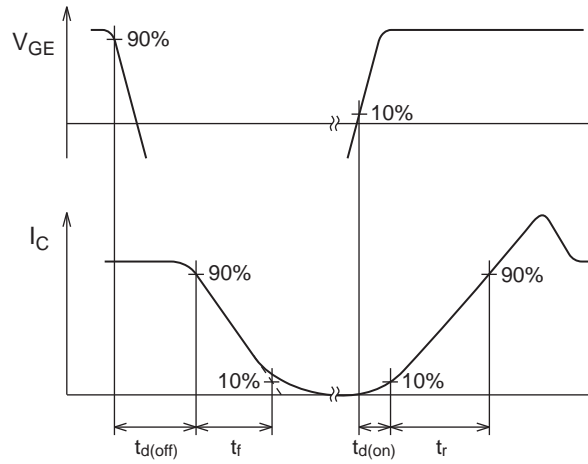




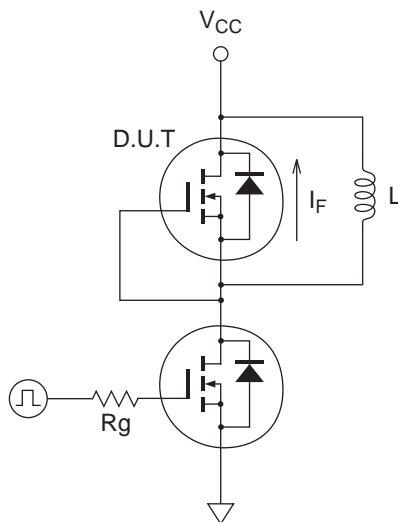
Switching Time Test Circuit



Waveform



Diode Reverse Recovery Time Test Circuit



Waveform



Package Dimension

| Package Name | JEITA Package Code | RENESAS Code | Previous Code | MASS[Typ.] | Unit: mm |
|--------------|--------------------|--------------|---------------|------------|----------|
| TO-247 | — | PRSS0003ZE-A | — | 6.0g | |

Ordering Information

| Orderable Part Number | Quantity | Shipping Container |
|-----------------------|----------|--------------------|
| RJH1CV7DPQ-E0#T2 | 450 pcs | Box (Tube) |

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